## **IN THE CLAIMS:**

The status of the claims is as follows:

- 1. (Original) A solid state device comprising:
  - a first material;
  - a second material;
- a barrier layer formed between the first material and the second material to prevent diffusion between the first material and the second material, the barrier layer includes a metal form of at least one of Ru and Re.
- 2. (Original) The device as recited in claim 1, wherein the metal form includes a hexagonal close packed structure.
- 3. (Original) The device as recited in claim 1, wherein the first material is a dielectric and the second material is a metal.
- 4. (Original) The device as recited in claim 1, wherein the first material is a conductor and the second material is a metal.
  - 5. (Original) The device as recited in claim 1, wherein the first material includes copper.
  - 6. (Original) The device as recited in claim 1, wherein the metal form includes a single

metallic phase in a temperature range of between about 300 degrees C and about 550 degrees C.

- 7. (Original) The device as recited in claim 1, wherein the metal form includes a single metallic phase in a temperature range of between about 300 degrees C and about 900 degrees C.
- 8. (Original) The device as recited in claim 1, wherein device is a semiconductor device and the first material includes a semiconductor material.
- 9. (Original) The device as recited in claim 1, wherein the barrier layer includes a thickness of 700 Angstroms or less.

10-20. (Cancelled)

- 21. (New) A solid state device comprising:
- a first material;
- a second material;
- a barrier layer formed between the first material and the second material to prevent diffusion between the first material and the second material, the barrier layer includes a metal form of Ru.
  - 22. (New) A solid state device comprising:
  - a first material;
  - a second material;

a barrier layer formed between the first material and the second material to prevent diffusion between the first material and the second material, the barrier layer includes a metal form of Re.